

REMARKS

Pages 4 and 8 are amended as supported by original Claims 3 and 4. Page 9 was amended to recite an "interdiction" zone. An interdiction zone is also mentioned at page 7 first paragraph.

The claims have been amended to delete the multiple dependent claim status and correct antecedent basis.

Moreover, Claims 2 and 6 were amended to insert the term "at least" before the second N-channel transistor, as supported at page 4, line 1. Claim 7 is supported at page 11, next to last paragraph. Claim 9 was amended to change "6" to "8" as supported at page 8, line 33.

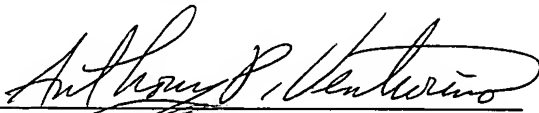
New Claim 14 is supported by original Claim 6. New Claim 15 is supported by original Claim 7. It is respectfully submitted no new matter is presented by the above amendments.

Early and favorable consideration of this application is respectfully requested.

Respectfully submitted,

Date: March 19, 2004

By:


Anthony P. Venturino
Registration No. 31,674

APV/pgw
ATTORNEY DOCKET NO. APV31683

STEVENS, DAVIS, MILLER & MOSHER, L.L.P.
1615 L STREET, N.W., SUITE 850
WASHINGTON, D.C. 20036
TEL. 202-785-0100 / FAX. 202-408-5200

ATTACHMENT I – Abstract

Photo-sensitive element for electro-optical sensors, including a photo-sensitive reception member, a current conversion circuit to convert the current generated by the photo-sensitive reception member into a tension signal, and an amplification and reading circuit. In at least one embodiment, the current conversion circuit comprises a P-channel transistor used as an ideal key and piloted with a tension that can vary between a high feed tension and a low feed tension. The photo-sensitive element is taken to a reset state if the pilot tension of the transistor is low, and to an integration state if the pilot tension is high.